


 ALTERNATIVE TO PTO/SB/08A/B  
 (Based on PTO 03-08 version)

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/537,804
				Filing Date	June 7, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	1792
				Examiner Name	F.C. Hiteshew
				Attorney Docket Number	204552035400
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Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
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Examiner Signature	/Felisa Hiteshew/	Date Considered	10/07/2008
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